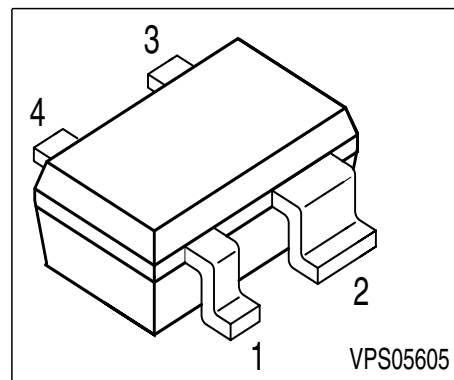


NPN Silicon Germanium RF Transistor

Preliminary data

- For high power amplifiers
- Ideal for low phase noise oscillators
- Maxim. available Gain $G_{ma} = 21$ dB at 1.8 GHz
Noise figure $F = 0.9$ dB at 1.8 GHz
- Gold metallization for high reliability
- 70 GHz f_T - Silicon Germanium technology



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP650	R5s	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	4	V
Collector-emitter voltage	V_{CES}	13	
Collector-base voltage	V_{CBO}	13	
Emitter-base voltage	V_{EBO}	1.2	
Collector current	I_C	150	mA
Base current	I_B	10	
Total power dissipation ¹⁾ $T_S \leq 75^\circ\text{C}$	P_{tot}	500	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	≤ 140	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 3\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4	4.5	-	V
Collector-emitter cutoff current $V_{CE} = 13\text{ V}, V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5\text{ V}, I_C = 0$	I_{EBO}	-	-	10	μA
DC current gain $I_C = 80\text{ mA}, V_{CE} = 3\text{ V}$	h_{FE}	100	180	320	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

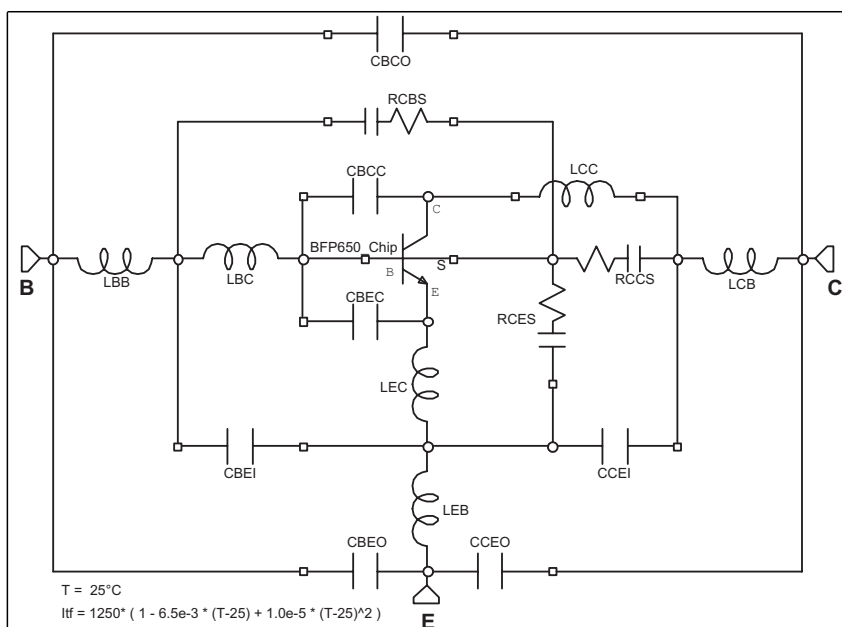
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1\text{ GHz}$	f_T	-	37	-	GHz
Collector-base capacitance $V_{CB} = 3\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	0.26	-	pF
Collector emitter capacitance $V_{CE} = 3\text{ V}$, $f = 1\text{ MHz}$	C_{ce}	-	0.45	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	1.1	-	
Noise figure $I_C = 10\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$ $I_C = 10\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 6\text{ GHz}$, $Z_S = Z_{Sopt}$	F	- -	0.8 1.9	- -	dB
Power gain, maximum available ¹⁾ $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 6\text{ GHz}$	G_{ma}	- -	21 10.5	- -	
Transducer gain $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$ $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 6\text{ GHz}$	$ S_{21e} ^2$	- -	17 6	- -	
Third order intercept point at output ²⁾ $V_{CE} = 3\text{ V}$, $I_C = 80\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\text{ }\Omega$	IP_3	-	29.5	-	dBm
1dB Compression point at output $I_C = 80\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	18	-	

¹⁾ $G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$
²⁾ IP_3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is $50\ \Omega$ from 0.1 MHz to 6 GHz

SPICE Parameter (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax):
Transistor Chip Data:

IS =	0.61	fA	BF =	450	-	NF =	1.025	-
VAF =	1000	V	IKF =	0.47	A	ISE =	62	fA
NE =	2	-	BR =	42	-	NR =	1	-
VAR =	2	V	IKR =	18	mA	ISC =	700	fA
NC =	1.8	-	RB =	1.036	Ω	IRB =	4.548	mA
RBM =	0.895	Ω	RE =	0.2	-	RC =	1.006	Ω
CJE =	682.5	fF	VJE =	0.8	V	MJE =	0.3	-
TF =	1.9	ps	XTF =	10	-	VTF =	1.5	V
ITF =	1.25	A	PTF =	0	deg	CJC =	204.6	fF
VJC =	0.6	V	MJC =	0.5	-	XCJC =	1	-
TR =	0.2	ns	CJS =	294.9	fF	VJS =	0.6	V
MJS =	0.27	-	XTB =	-1.42	-	EG =	1.078	eV
XTI =	3	-	FC =	0.8		TNOM	298	K
AF =	2	-	KF =	2.441E-11				
TITF1	-0.0065	-	TITF2	1.0E-5				

All parameters are ready to use, no scaling is necessary. Extracted on behalf of Infineon Technologies AG by:
Institut für Mobil- und Satellitentechnik (IMST)

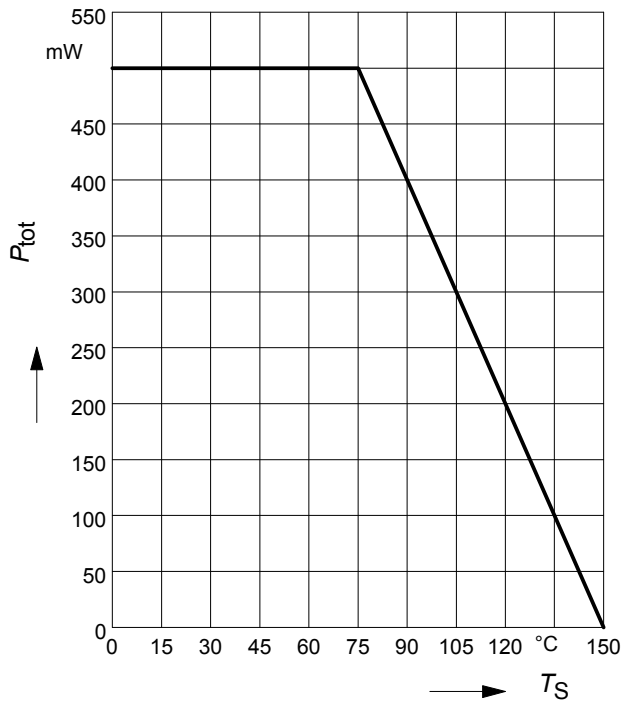
Package Equivalent Circuit:


LBC =	50	pH
LCC =	50	pH
LEC =	4	pH
LBB =	554.6	pH
LCB =	606.9	pH
LEB =	138.7	pH
CBEC =	327.6	fF
CBCC =	171.4	fF
CES =	490	fF
CBS =	120	fF
CCS =	135	fF
CBCO =	7.5	fF
CCEO =	112.6	fF
CBEO =	121.5	fF
CCEI =	5.7	fF
CBEI =	6.9	Ω
RBS =	710	Ω
RCS =	710	Ω
RES =	140	Ω

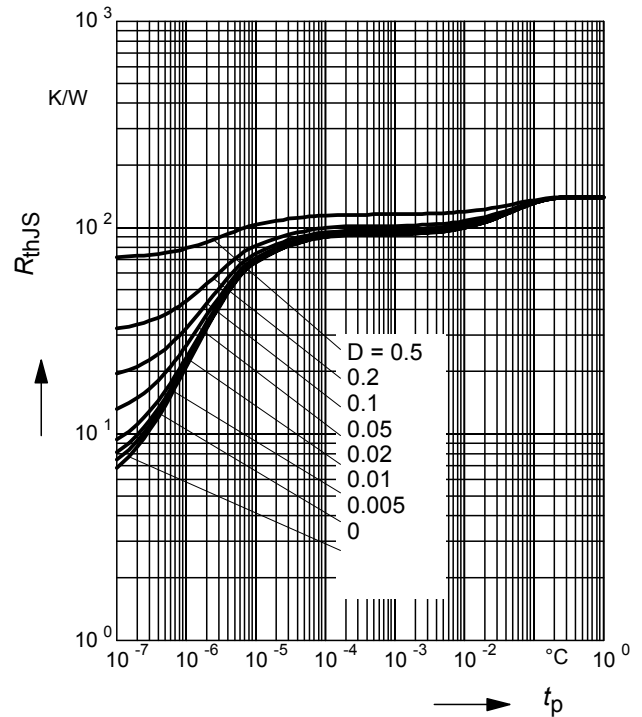
Valid up to 6GHz

For examples and ready to use parameters
please contact your local Infineon Technologies
distributor or sales office to obtain a Infineon
Technologies CD-ROM or see Internet:
<http://www.infineon.com/silicondiscretes>

Total power dissipation $P_{\text{tot}} = f(T_S)$

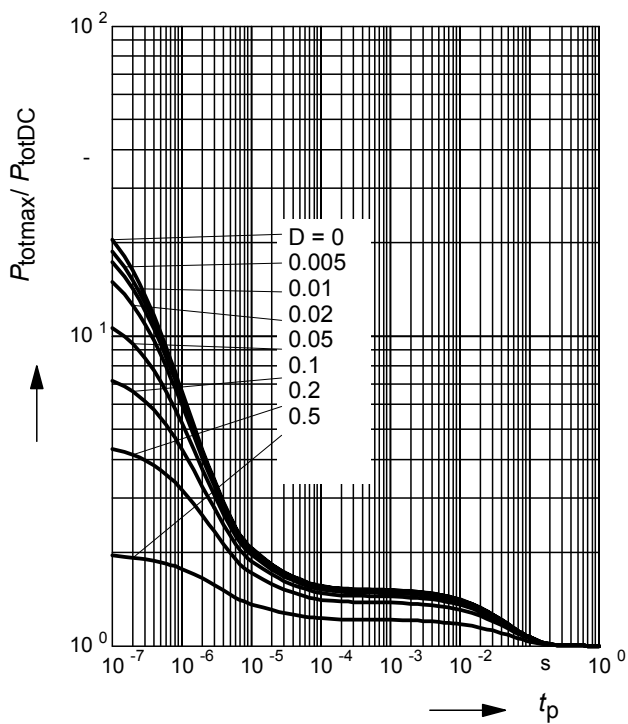


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



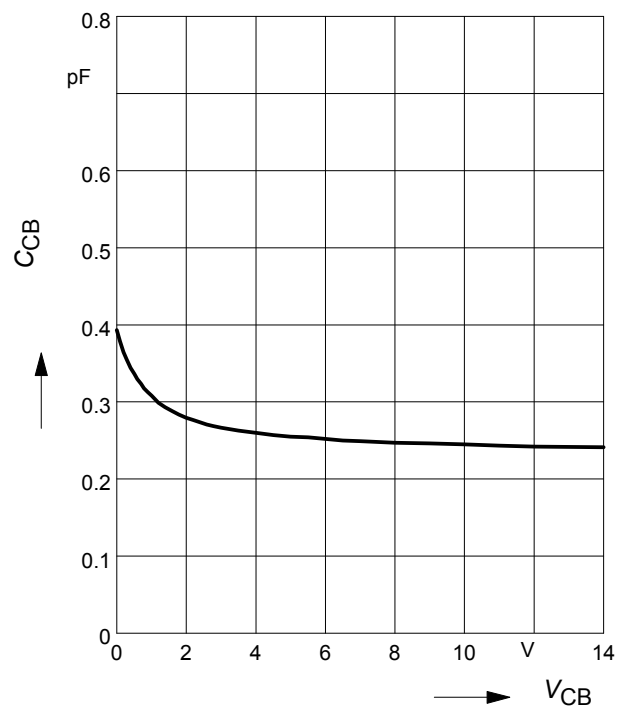
Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



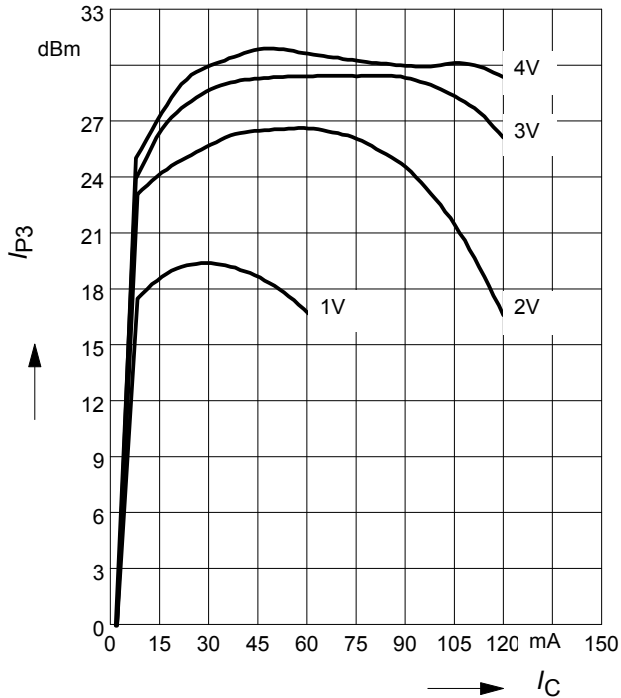
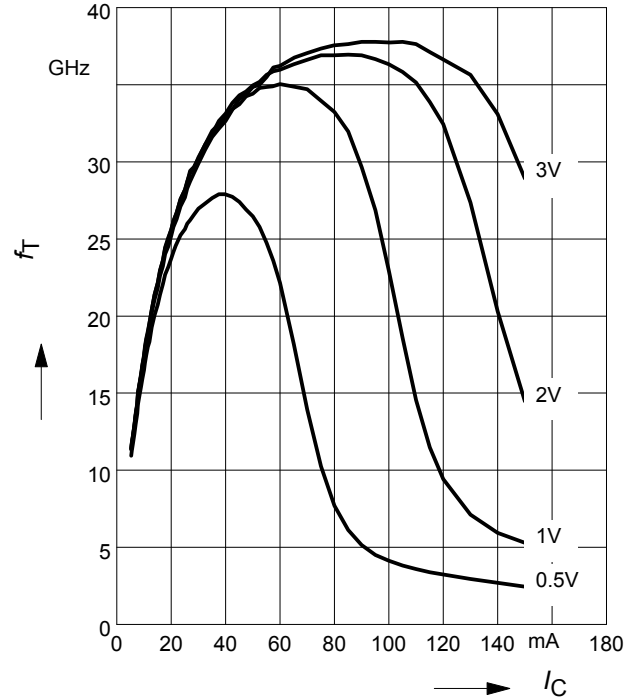
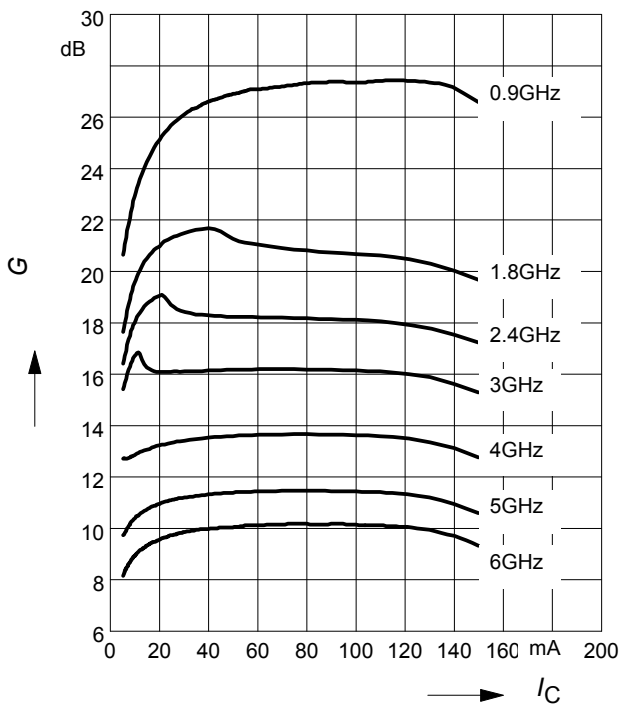
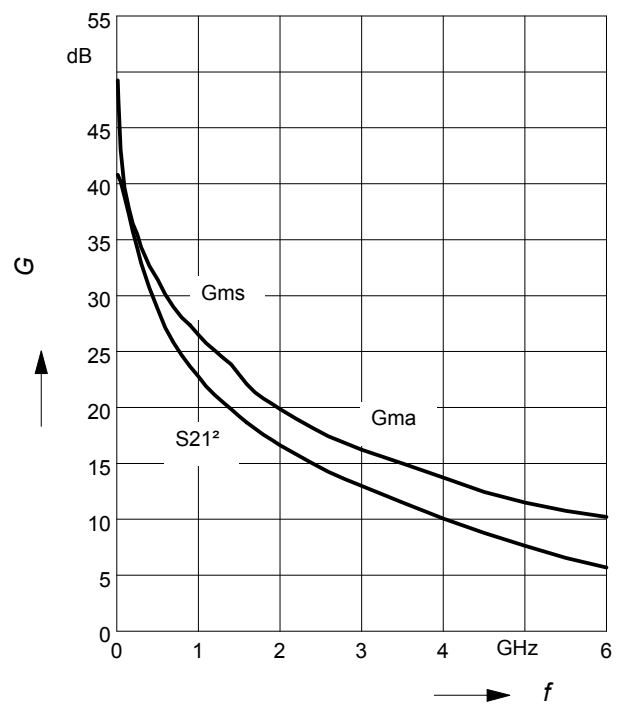
Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$

$f = 1\text{MHz}$



Third order Intercept Point $IP_3 = f(I_C)$

 (Output, $Z_S = Z_L = 50\Omega$)

 V_{CE} = parameter, $f = 1.8\text{ GHz}$

Transition frequency $f_T = f(I_C)$
 $f = 1\text{ GHz}$
 V_{CE} = parameter

Power gain $G_{ma}, G_{ms} = f(I_C)$
 $V_{CE} = 3\text{ V}$
 f = parameter

Power Gain $G_{ma}, G_{ms} = f(f)$
 $|S_{21}|^2 = f(f)$
 $V_{CE} = 3\text{ V}, I_C = 80\text{ mA}$


Power gain G_{ma} , $G_{ms} = f(V_{CE})$

$I_C = 80\text{mA}$

$f = \text{parameter}$

